

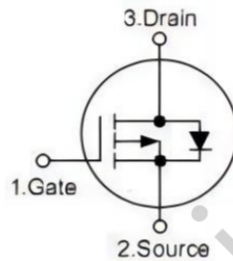
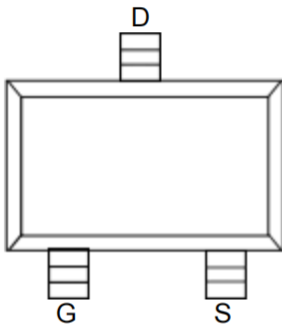
主要特性/Features

1. 开关速度快Fastswitchspeed
2. 导通电阻低Lowonresistance

应用/Application

用于一般开关和低压电源电路
 For general switch and low voltage power circuits

印字/MARKING等效电路/Equivalent Circuit



极限参数/Absolute Maximum Ratings (TA=25°C unless otherwise noted)

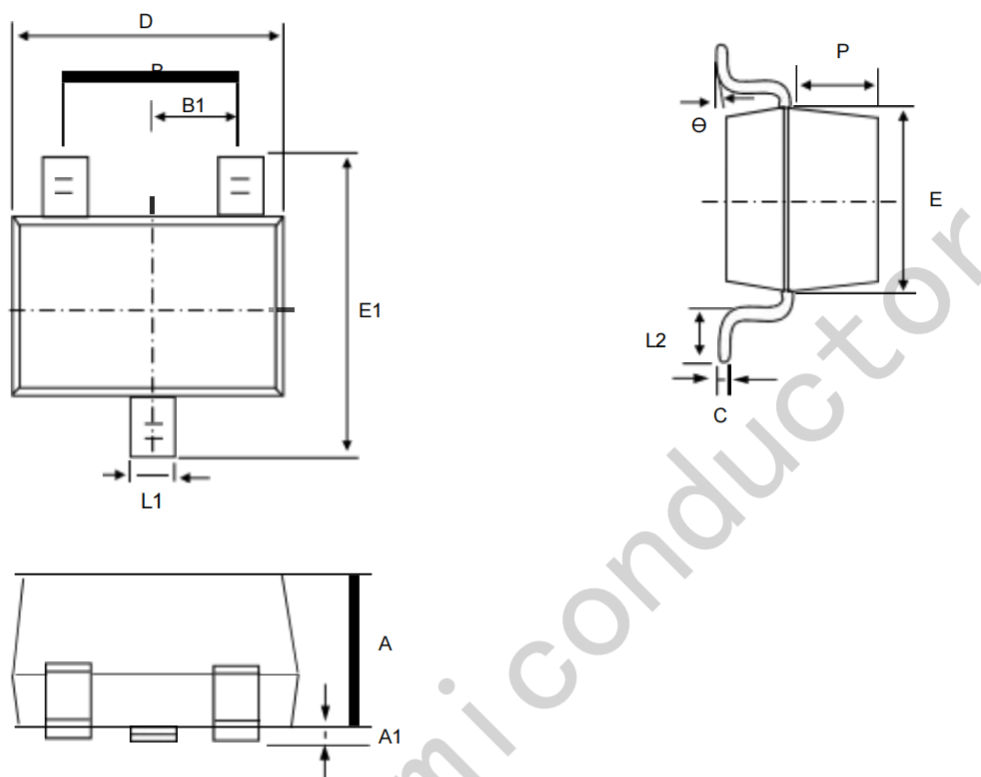
参数/Parameter	符号/Symbol	数值/Value	单位/Unit
漏极-源极电压/Drain-Source Voltage	V_{DS}	-20	V
栅极-源极电压/Gate-Source Voltage	V_{GS}	± 8	V
漏极电流 (持续) /Continuous Drain Current	I_D	-1.8	A
漏极电流 (脉冲) /Pulsed Drain Current	I_{DM}	-10	A
耗散功率/Power Dissipation	P_D	0.35	W
热阻/Thermal Resistance Junction to Ambient	$R_{\theta JA}$	350	$^{\circ}\text{C}/\text{mW}$
结温/Junction Temperature	T_j	150	$^{\circ}\text{C}$
储存温度/Storage Temperature	T_{stg}	-55 ~ 150	$^{\circ}\text{C}$

电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-1A V _{GS}	-	135	176	mΩ
		s=-2.5V, I _D =-1A	-	185	250	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	- 0.45	- 0.65	- 1.00	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-20V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate Leakage Current, Forward	V _{GS} =±12V, V _{DS} =0V	-	-	±10 0	nA
T _J , T _{STG}	Operating and Storage Temperature	-55 to 150°C Max				

JSMICRO Semiconductor

SOT-23 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
L1	0.350	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950TPY.		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600

单击下面可查看定价，库存，交付和生命周期等信息

[>>JSMSEMI\(杰盛微\)](#)